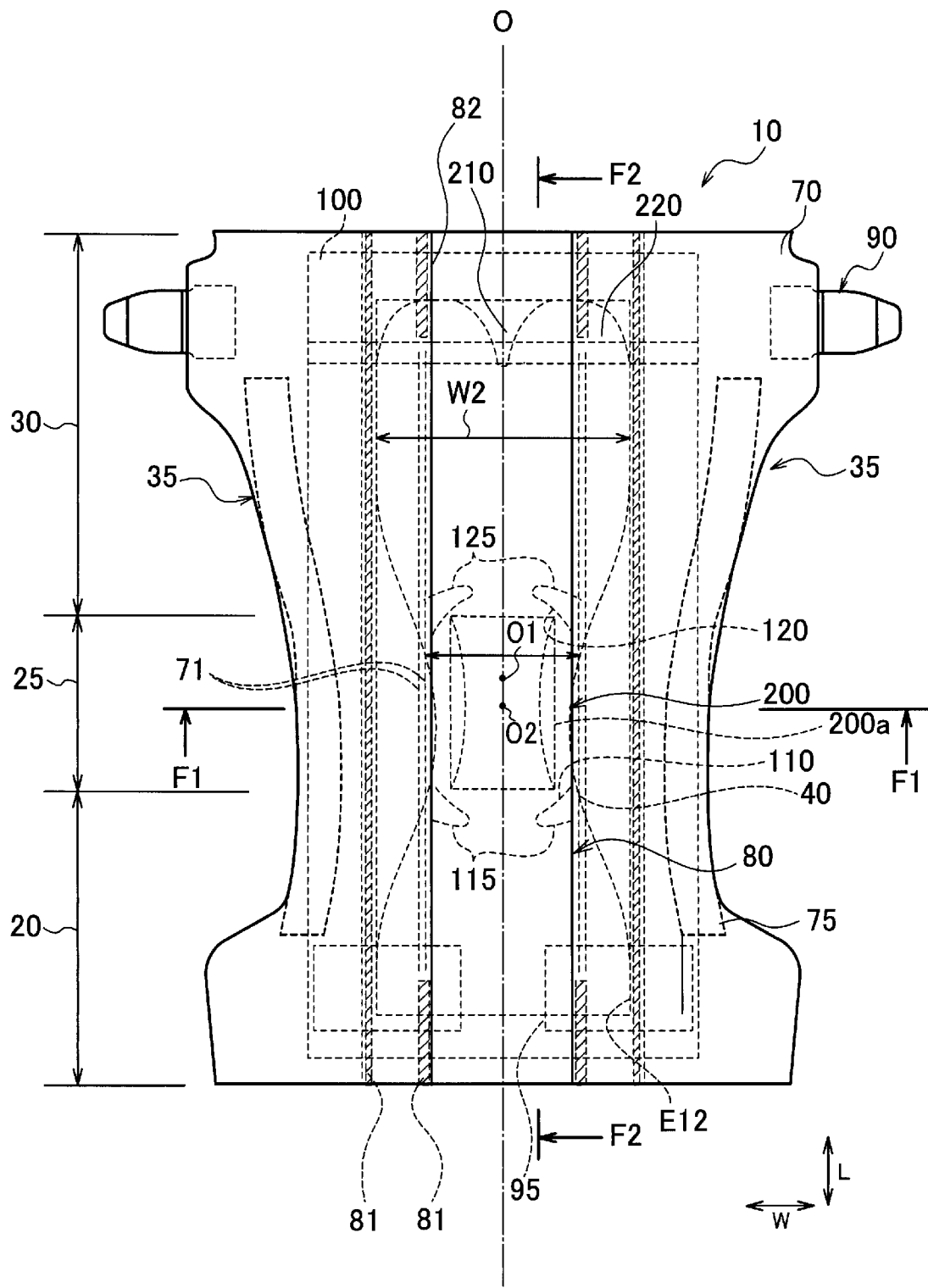
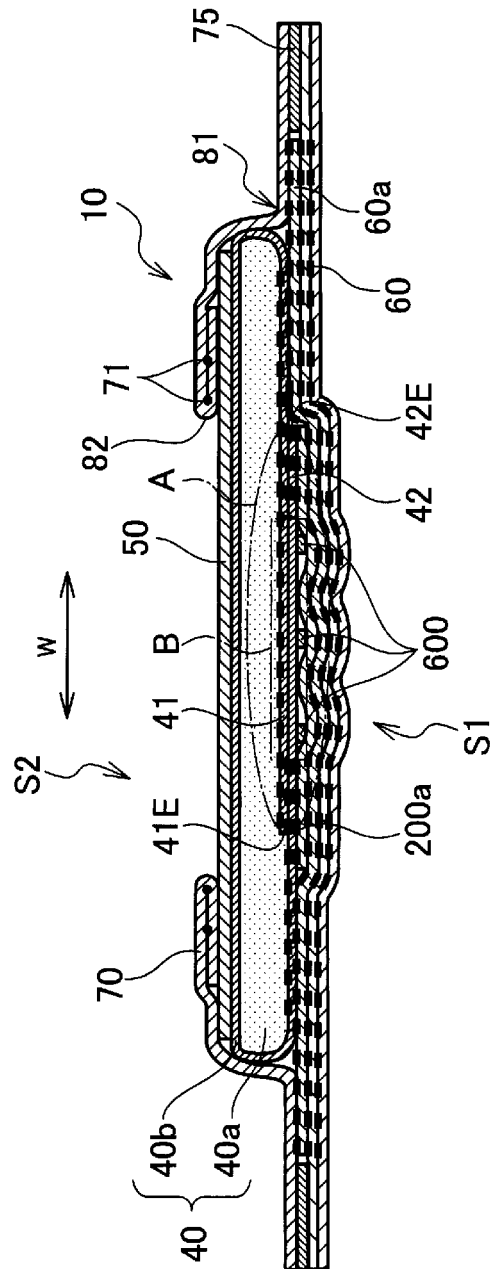


[図1]

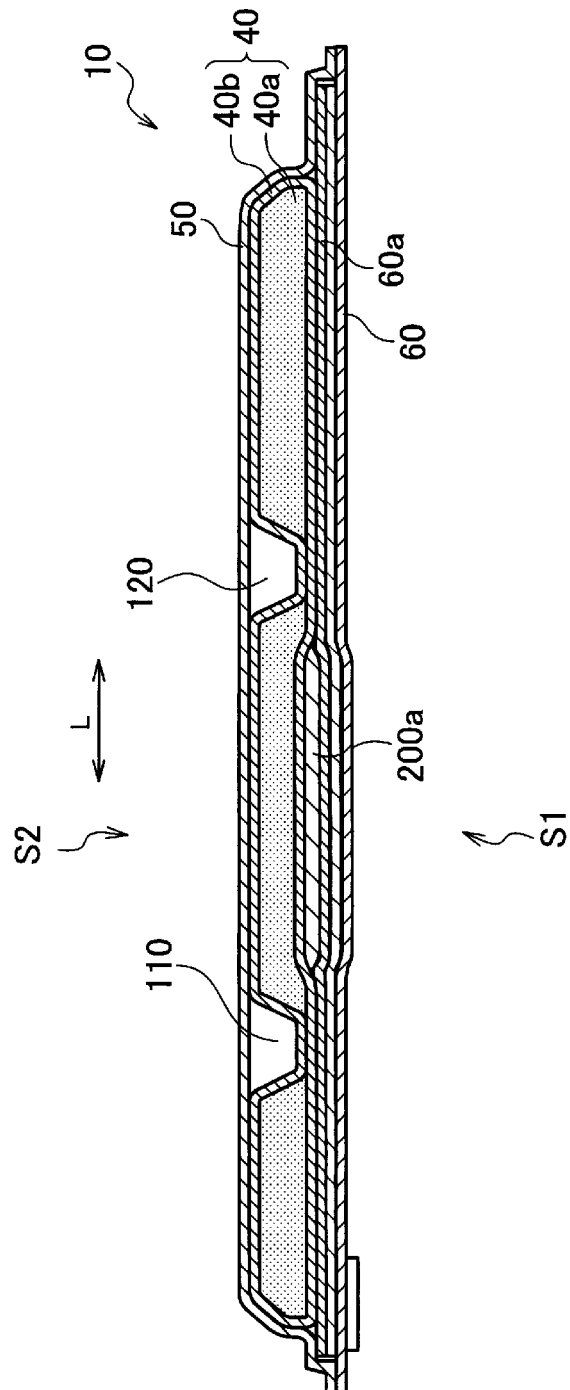




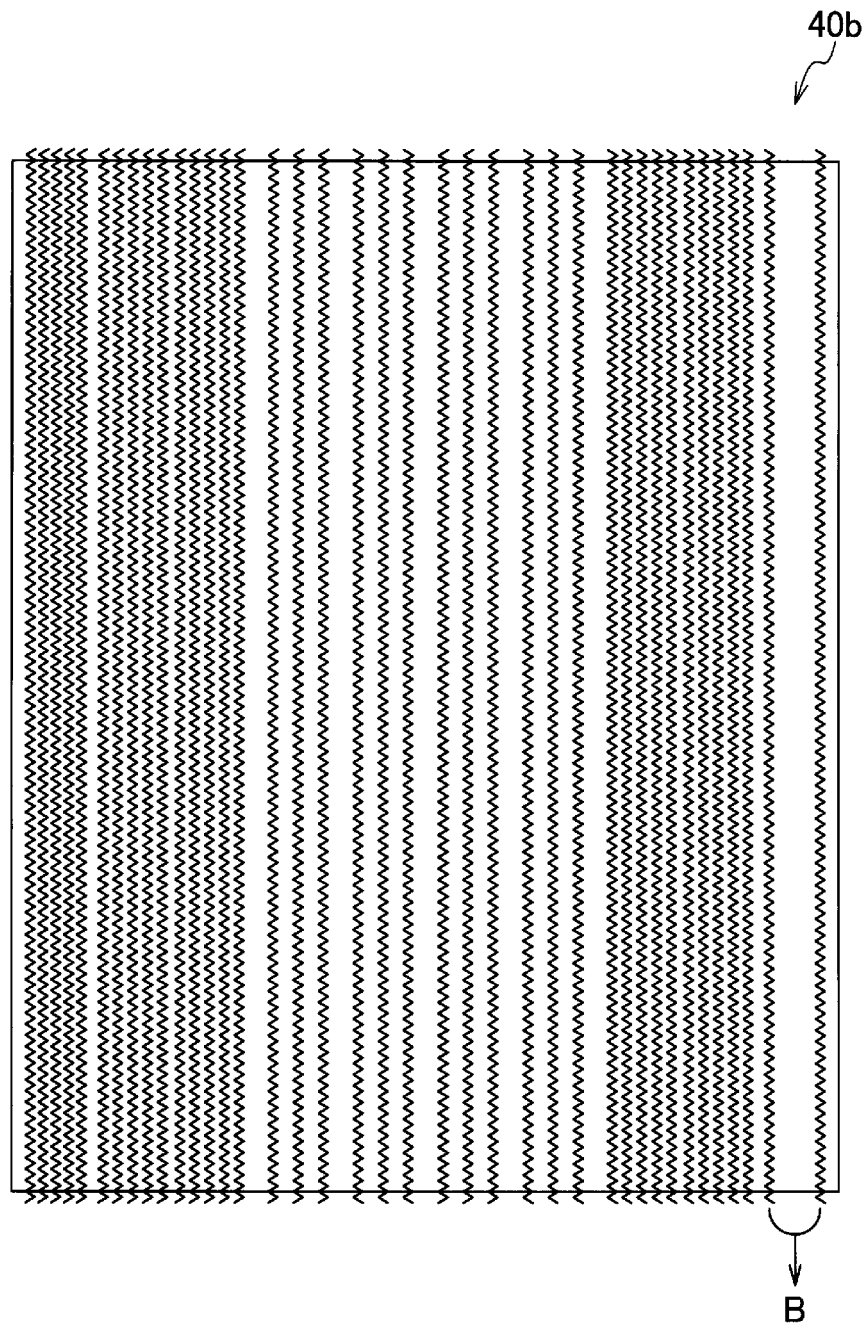
[図3]



[図4]

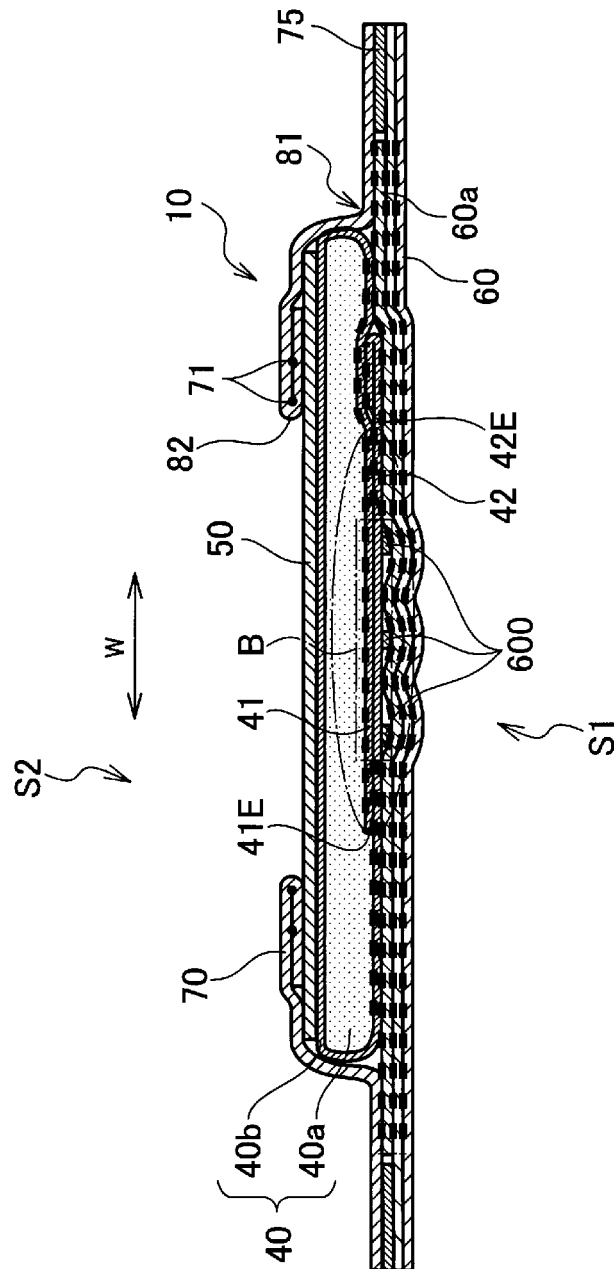


[図5]



A cross-sectional view of a semiconductor device. The device consists of a substrate 10 with a central region 40, a central layer 41, and a central region 42. The central region 40 is divided into two parts, 40a and 40b, by a central layer 41. The central region 42 is a layer on top of the central layer 41. The device is shown in a cross-sectional view with various layers and regions labeled with reference numerals. A width W is indicated by a double-headed arrow. The device is shown in a cross-sectional view with various layers and regions labeled with reference numerals.

[図7]



[図8]

